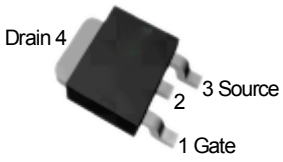
Features

- 100V/88A
  $R_{DS(ON)}$=6.8mΩ(typ.)@V_{GS}=10V
  $R_{DS(ON)}$=7.8mΩ(typ.)@V_{GS}=4.5V
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)
- Moisture Sensitivity Level MSL1 (per JEDEC J-STD-020D)

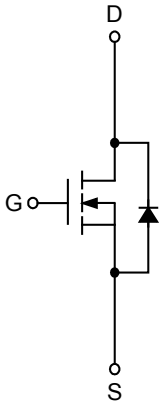
Applications

- Power Management for SMPS
- DC/DC Converter

Pin Description



Top View of TO-252-2



N-Channel MOSFET

Absolute Maximum Ratings (T_A=25°C Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V_{DSS}	Drain-Source Voltage		100	V
V_{GSS}	Gate-Source Voltage		±20	
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	
I_S	Diode Continuous Forward Current	T_C=25°C	88	A
I_D	Continuous Drain Current	T_C=25°C	88	A
		T_C=100°C	53	
I_{DM} [a]	Pulsed Drain Current	T_C=25°C	264	
P_D	Maximum Power Dissipation	T_C=25°C	125	W
		T_C=100°C	50	
$R_{\theta JC}$	Thermal Resistance-Junction to Case		1	°C/W
$R_{\theta JA}$ [c]	Thermal Resistance-Junction to Ambient		50	°C/W
I_{AS} [b]	Avalanche Current, Single pulse	L=0.5mH	27	A
E_{AS} [b]	Avalanche Energy, Single pulse	L=0.5mH	182	mJ

Note * : Calculated continuous current based on maximum allowable junction temperature. Bonding wire limitation current is 80A.
Note a : Pulse width limited by max. junction temperature.
Note b : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature T_j=25°C).
Note c : Surface Mounted on 1in^2 pad area.

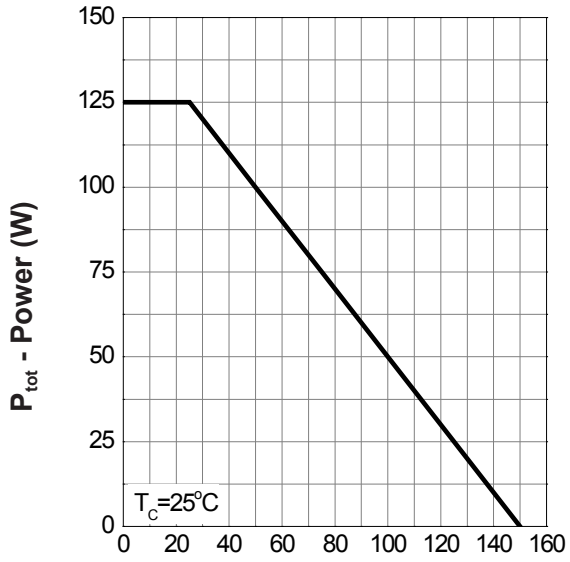
Electrical Characteristics (T_A= 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250μA	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=80V, V_{GS}=0V	-	-	1	μA
		T_J=85°C	-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250μA	1	2	3	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
$R_{DS(ON)}$ [d]	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=30A	-	6.8	8	mΩ
		V_{GS}=4.5V, I_{DS}=20A	-	7.8	11	
Diode Characteristics						
V_{SD} [d]	Diode Forward Voltage	I_{SD}=15A, V_{GS}=0V	-	0.8	1.3	V
t_{rr}	Reverse Recovery Time	I_{SD}=30A, dI_{SD}/dt=100A/μs	-	48	-	ns
Q_{rr}	Reverse Recovery Charge		-	90	-	nC
Dynamic Characteristics [e]						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V,F=1MHz	-	1.5	-	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=50V, Frequency=1.0MHz	-	3000	3900	pF
C_{oss}	Output Capacitance		-	410	-	
C_{rss}	Reverse Transfer Capacitance		-	40	-	
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=30V, R_L=30Ω, I_{DS}=1A, V_{GEN}=10V, R_G=6Ω	-	19	35	ns
t_r	Turn-on Rise Time		-	11	20	
$t_{d(OFF)}$	Turn-off Delay Time		-	70	126	
t_f	Turn-off Fall Time		-	75	135	
Gate Charge Characteristics [e]						
Q_g	Total Gate Charge	V_{DS}=50V, V_{GS}=10V, I_{DS}=30A	-	57	80	nC
Q_g	Total Gate Charge	V_{DS}=50V, V_{GS}=4.5V, I_{DS}=30A	-	28	-	
Q_{gs}	Gate-Source Charge		-	11	-	
Q_{gd}	Gate-Drain Charge		-	12	-	

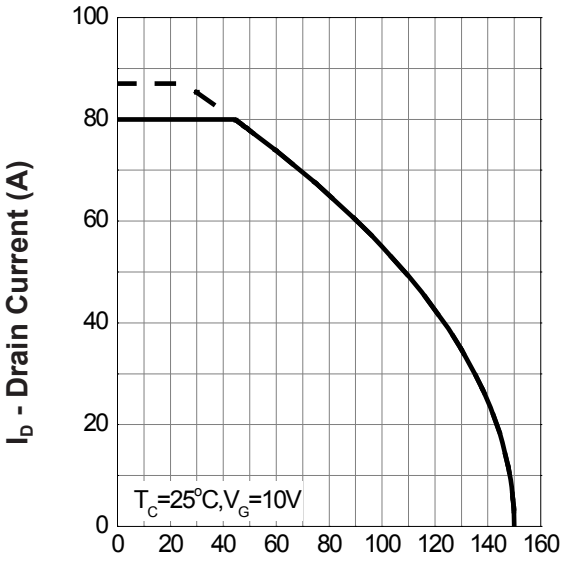
Note d：Pulse test ; pulse width≤300μs, duty cycle≤2%.
Note e：Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

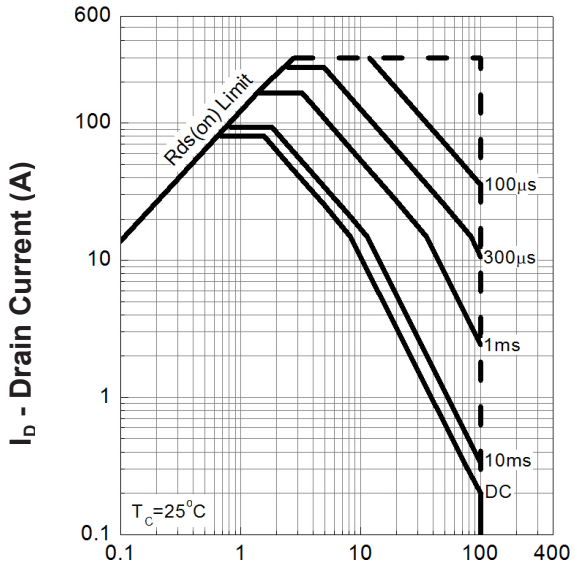
Power Dissipation



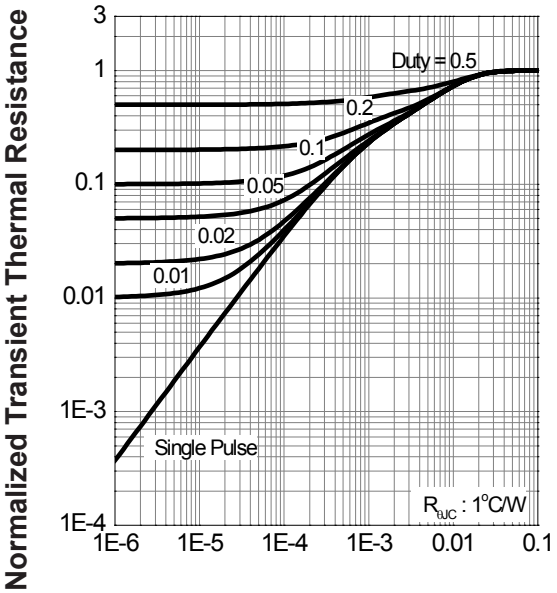
Drain Current



Safe Operation Area

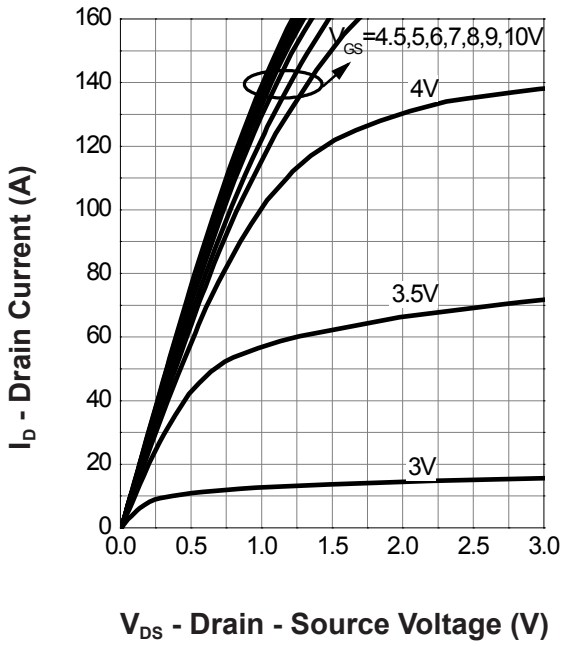


Thermal Transient Impedance

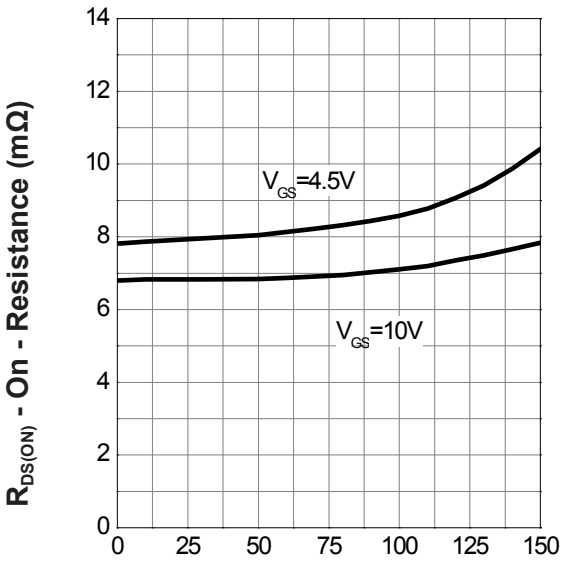


Typical Operating Characteristics(Cont.)

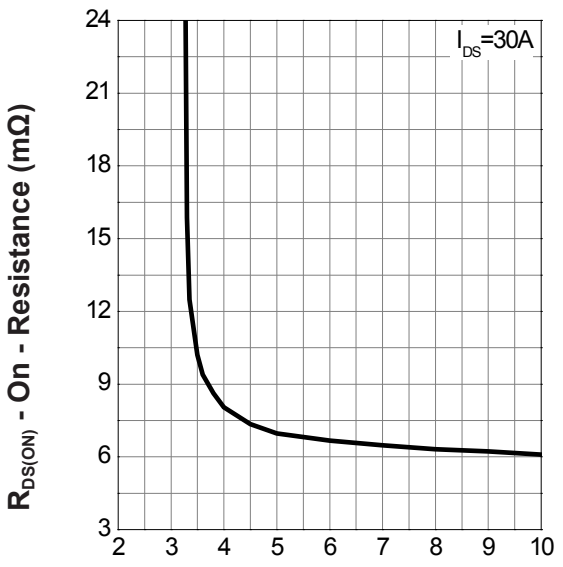
Output Characteristics



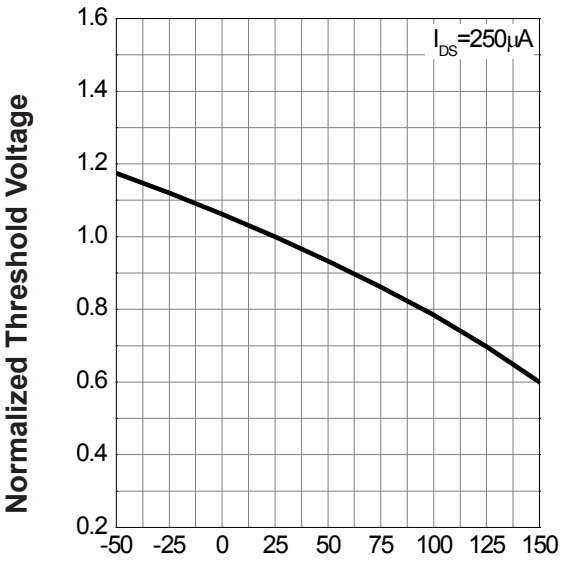
Drain-Source On Resistance



Gate-Source On Resistance

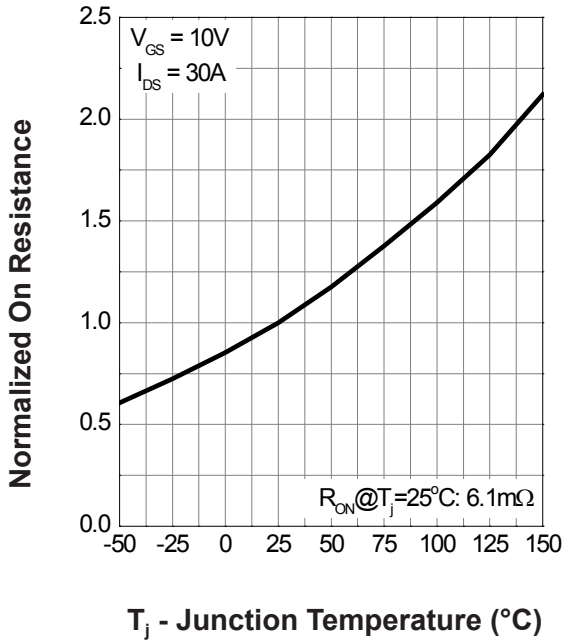


Gate Threshold Voltage

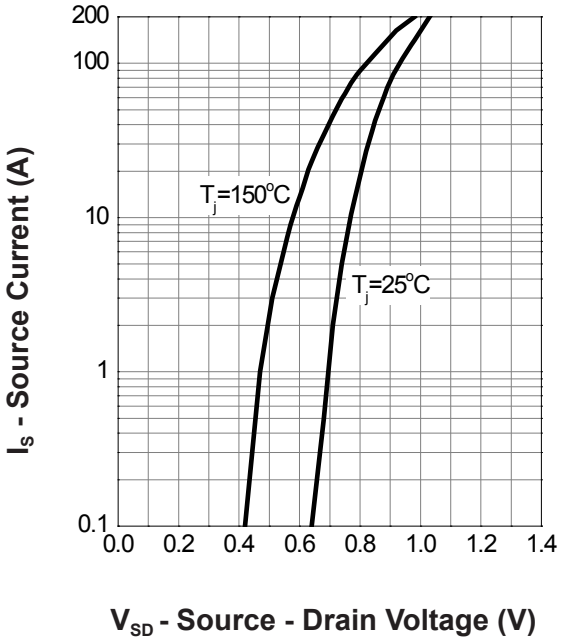


Typical Operating Characteristics(Cont.)

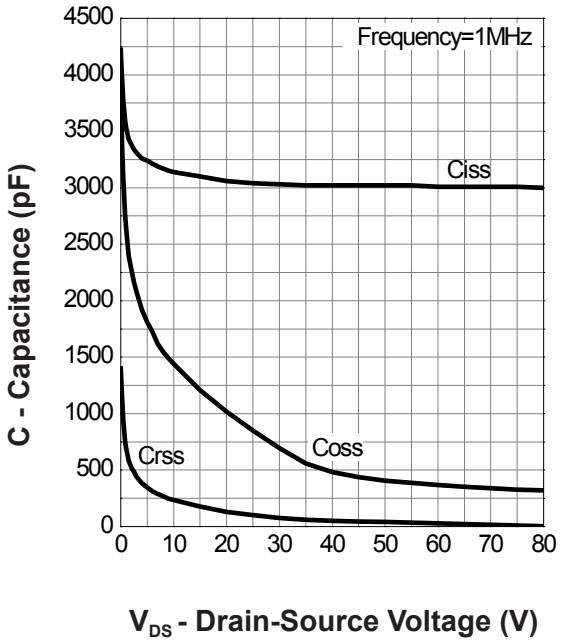
Drain-Source On Resistance



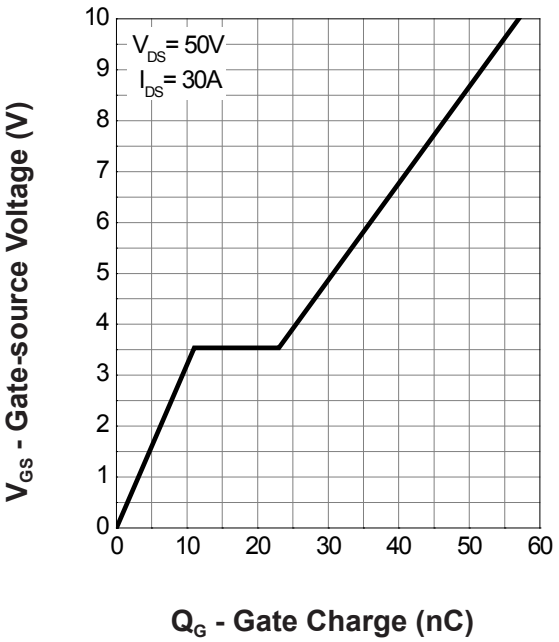
Source-Drain Diode Forward



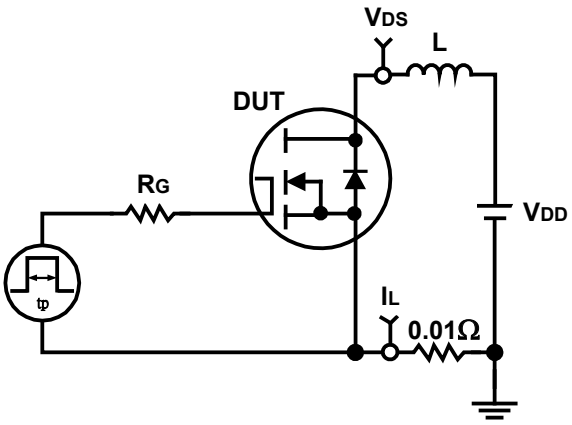
Capacitance

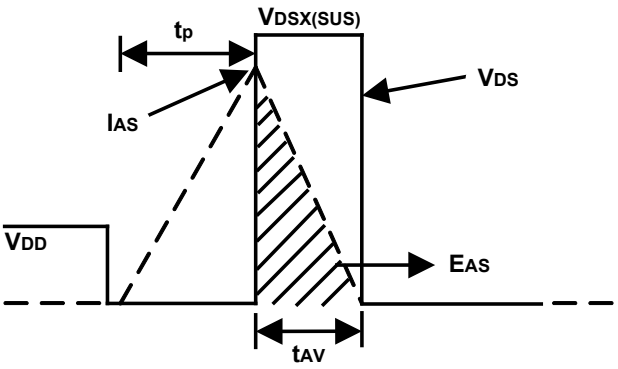


Gate Charge

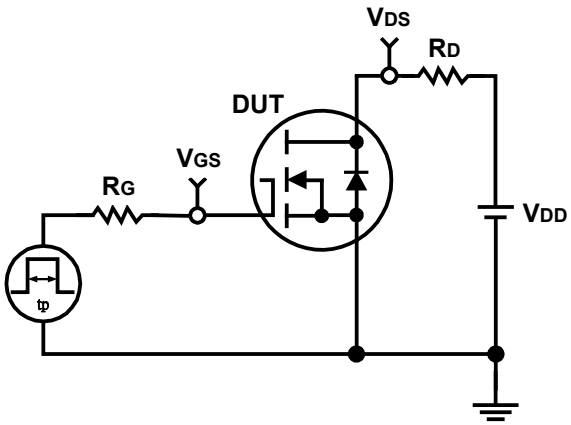


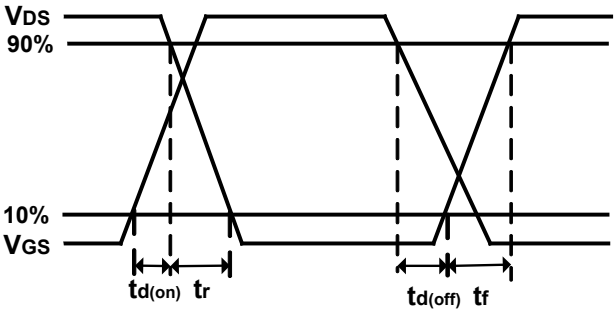
Avalanche Test Circuit and Waveforms





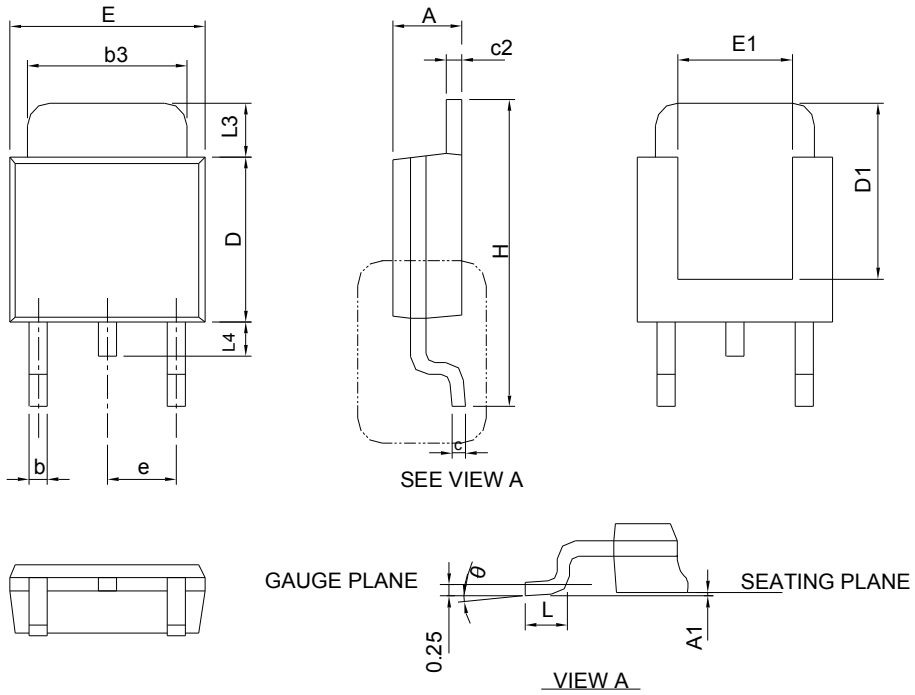
Switching Time Test Circuit and Waveforms





Package Information

TO-252-2



SYMBOL	TO-252-2			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1	-	0.13	-	0.005
b	0.50	0.89	0.020	0.035
b3	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.33	6.22	0.210	0.245
D1	4.57	6.00	0.180	0.236
E	6.35	6.73	0.250	0.265
E1	3.81	6.00	0.150	0.236
e	2.29 BSC		0.090 BSC	
H	9.40	10.41	0.370	0.410
L	0.90	1.78	0.035	0.070
L3	0.89	2.03	0.035	0.080
L4	-	1.02	-	0.040
θ	0°	8°	0°	8°

Note : Follow JEDEC TO-252-2 .

RECOMMENDED LAND PATTERN